

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D max $T_A = 25^\circ C$
30V	15m Ω @ $V_{GS} = 10V$	10.7A
	18.5m Ω @ $V_{GS} = 4.5V$	9.6A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

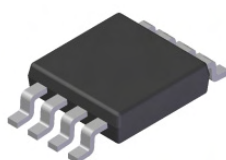
- DC-DC Converters
- Power management functions

Features

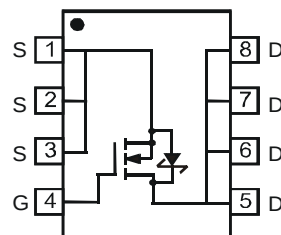
- DIOFET utilizes a unique patented process to monolithically integrate a MOSFET and a Schottky in a single die to deliver:
 - Low $R_{DS(on)}$ - minimizes conduction losses
 - Low V_{SD} - reducing the losses due to body diode conduction
 - Low Q_{rr} - lower Q_{rr} of the integrated Schottky reduces body diode switching losses
 - Low gate capacitance (Q_g/Q_{gs}) ratio – reduces risk of shoot-through or cross conduction currents at high frequencies
 - Avalanche rugged – I_{AR} and E_{AR} rated
- **Lead Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **ESD Protected**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (approximate)

Top View



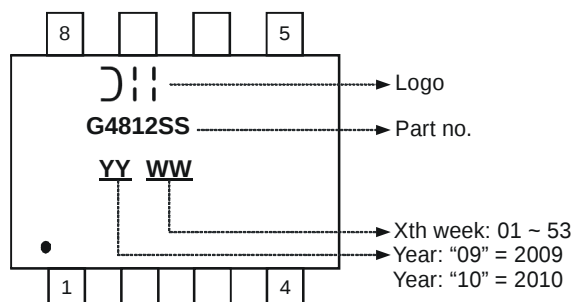
Top View
Internal Schematic

Ordering Information (Note 3)

Part Number	Case	Packaging
DMG4812SSS-13	SO-8	2500 / Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 4) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 85°C	I _D	8 6.4	A
Continuous Drain Current (Note 5) V _{GS} = 10V	t ≤ 10 sec	T _A = 25°C T _A = 85°C	I _D	10.7 8.6	A
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t ≤ 10 sec	T _A = 25°C T _A = 85°C	I _D	9.6 7.7	A
Pulsed Drain Current (Note 6)			I _{DM}	45	A
Avalanche Current (Notes 6 & 7)			I _{AR}	13	A
Repetitive Avalanche Energy (Notes 6 & 7) L = 0.3mH			E _{AR}	25.4	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	1.54	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	R _{θJA}	81	°C/W
Power Dissipation (Note 5)	P _D	2.8	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 5)	R _{θJA}	45	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise stated

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	150	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.0	-	2.3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	11	15	mΩ	V _{GS} = 10V, I _D = 10.7A
		-	16.5	18.5		V _{GS} = 4.5V, I _D = 9.6A
Forward Transfer Admittance	Y _{fs}	-	20	-	S	V _{DS} = 5V, I _D = 10.7A
Diode Forward Voltage	V _{SD}	-	0.36	0.5	V	V _{GS} = 0V, I _S = 1A
Maximum Body-Diode + Schottky Continuous Current	I _S	-	-	5	A	-
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	1849	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	158	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	123	-	pF	
Gate Resistance	R _g	0.54	2.0	4.0	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge V _{GS} = 4.5V	Q _g	-	18.5	-	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 9.6A
Total Gate Charge V _{GS} = 10V	Q _g	-	43	-	nC	
Gate-Source Charge	Q _{gs}	-	4.7	-	nC	
Gate-Drain Charge	Q _{gd}	-	4.0	-	nC	
Turn-On Delay Time	t _{D(on)}	-	6.62	-	ns	V _{GS} = 10V, V _{DS} = 15V, R _G = 3Ω, R _L = 15Ω, I _D = 1A
Turn-On Rise Time	t _r	-	8.73	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	36.41	-	ns	
Turn-Off Fall Time	t _f	-	4.69	-	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout. The value in any given application depends on the user's specific board design.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 1 oz. Copper, single sided, device is measured at t ≤ 10 sec.
 - Repetitive rating, pulse width limited by junction temperature.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = 25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

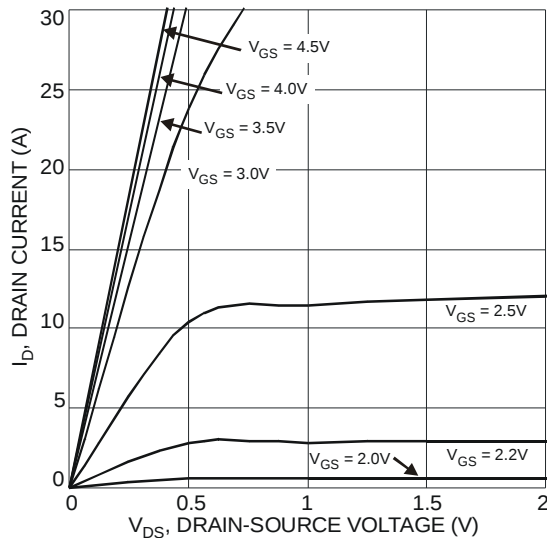


Fig. 1 Typical Output Characteristic

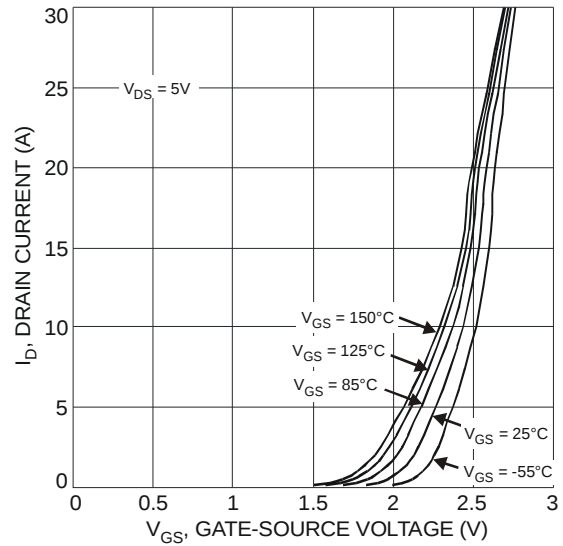


Fig. 2 Typical Transfer Characteristic

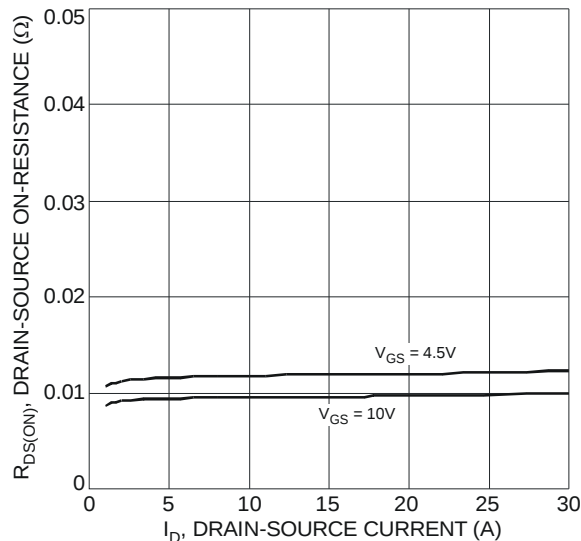


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

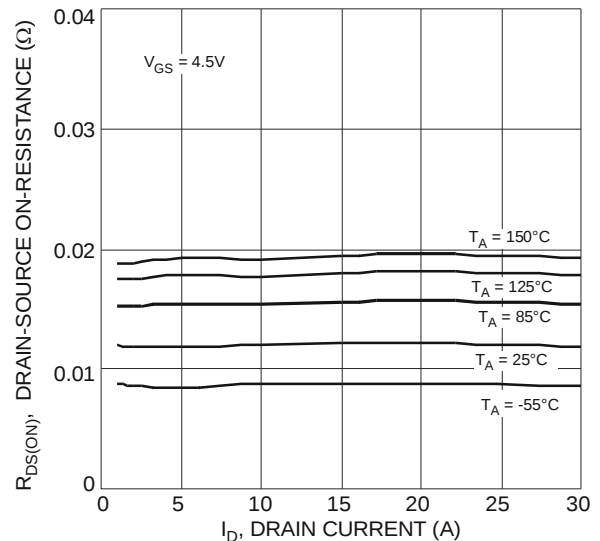


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

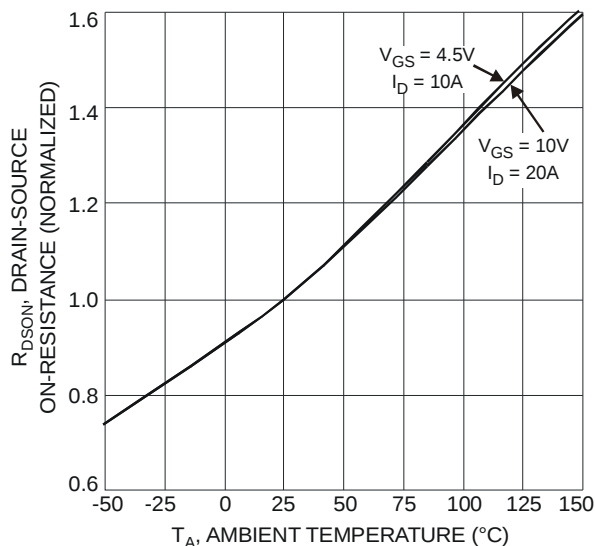


Fig. 5 On-Resistance Variation with Temperature

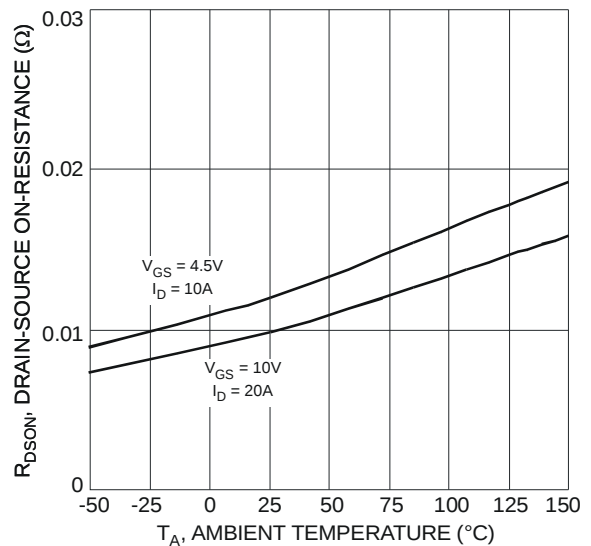


Fig. 6 On-Resistance Variation with Temperature

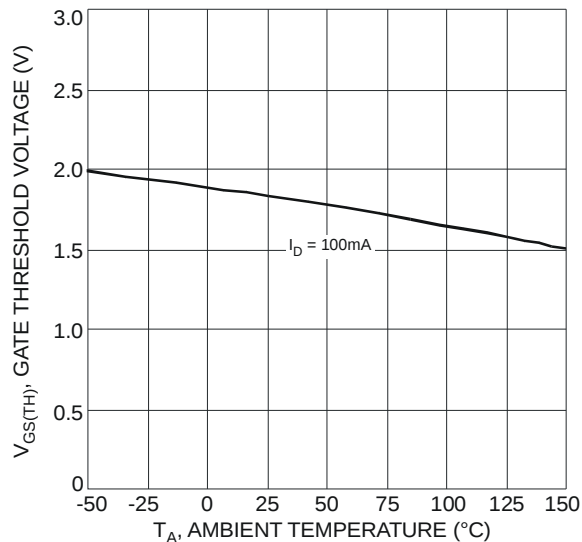


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

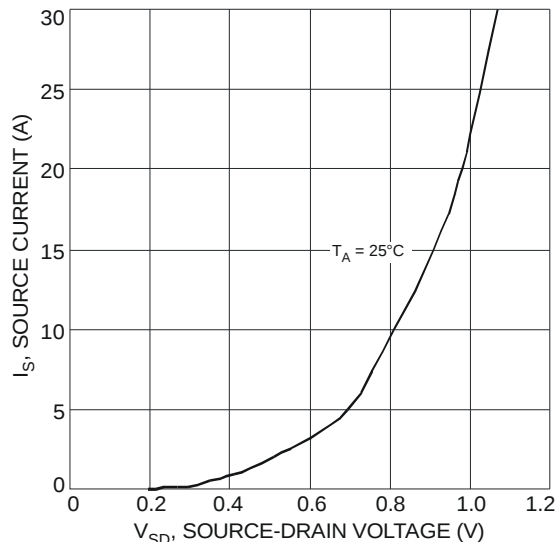


Fig. 8 Diode Forward Voltage vs. Current

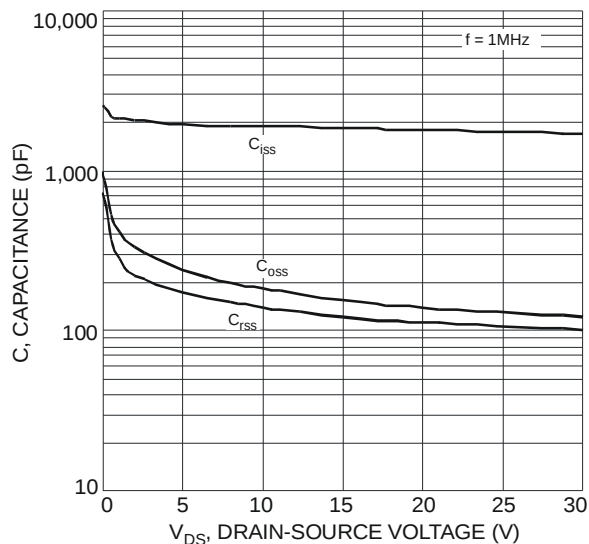


Fig. 9 Typical Total Capacitance

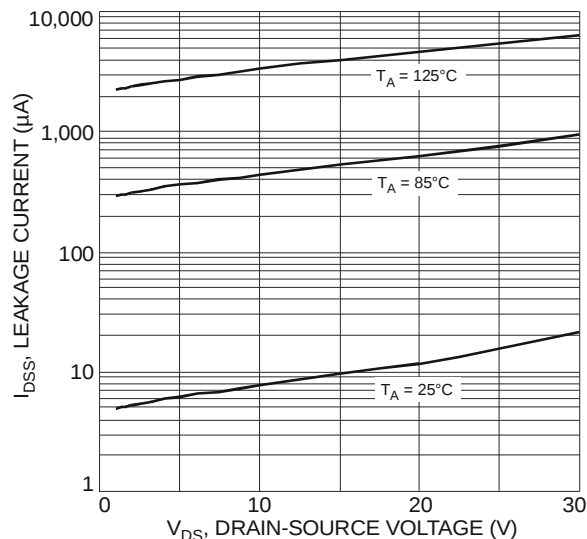


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

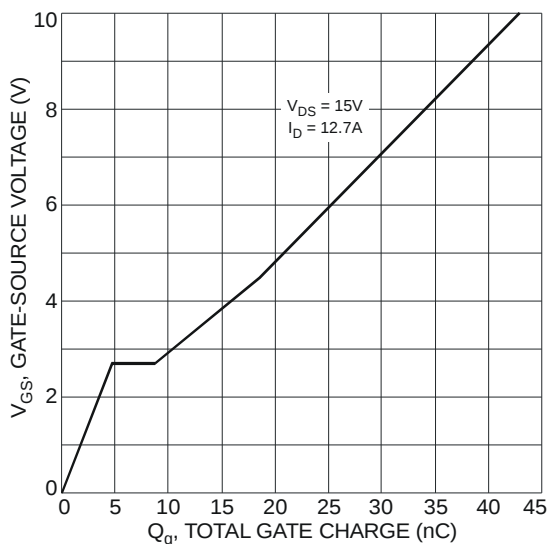
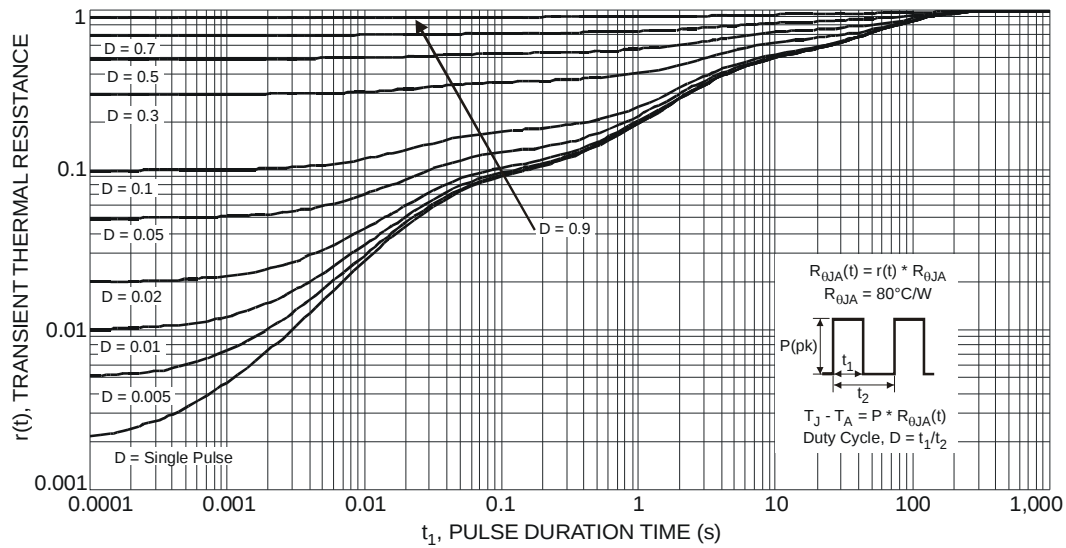
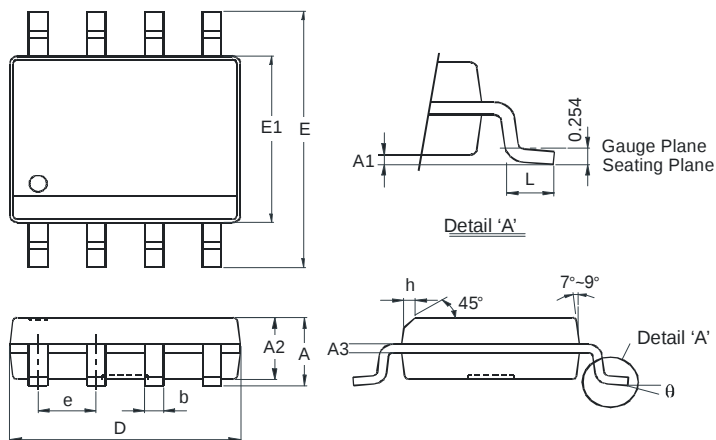


Fig. 11 Gate-Charge Characteristics

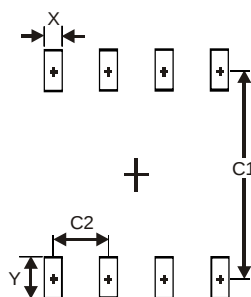


Package Outline Dimensions



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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